



K. Memory (Design & Process Technology) 분과

2021년 1월 27일(수), 13:00-14:30 / 채널 D

[WD3-K] NAND Flash Memory

좌장: 강명곤 교수 (한국교통대학교), 김윤 교수 (서울시립대학교)

WD3-K-1 13:00-13:15	D₂ High Pressure Annealing Effect on Silicon Nitride in Flash Memory Jae-Young Sung, Jun-Kyo Jeong, Woon-San Ko, Ki-Ryung Nam, and Ga-Won Lee <i>Department of Electronics, Chungnam National University</i>
WD3-K-2 13:15-13:30	철회
WD3-K-3 13:30-13:45	Analysis of Memory Characteristics Change According to the Roughness of the Layer Jun-Kyo Jeong, Jae-Young Sung, Woon-San Go, Ki-Ryeong Nam, and Ga-Won Lee <i>Department of Electronic Engineering, Chungnam National University</i>
WD3-K-4 13:45-14:00	평균트랩거리를 변수로 사용한 전하 트랩 플래시 메모리의 프로그램 모델 김건웅, 백승재 <i>Faculty of Electronic and Electrical Engineering, Hankyong National University</i>
WD3-K-5 14:00-14:15	CTF (Charge-Trap Flash) 메모리 기반 채널 적층형 3차원 시냅스 어레이 Jung Nam Kim, Hyun-Seok Choi, Boram Kim, Ji-Hoon Ahn, Jun Park, and Yoon Kim <i>Department of Electrical and Computer Engineering, University of Seoul</i>
WD3-K-6 14:15-14:30	Demonstration of Multi-layered Macaroni Filler for Improvement of Erase Efficiency in 3-D V-NAND Dae-Han Jung ¹ , Dae-Hwan Yun ² , Hagyoul Bae ³ , and Jun-Young Park ¹ <i>¹Chungbuk National University, ²SK Hynix Inc., ³Purdue University</i>

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